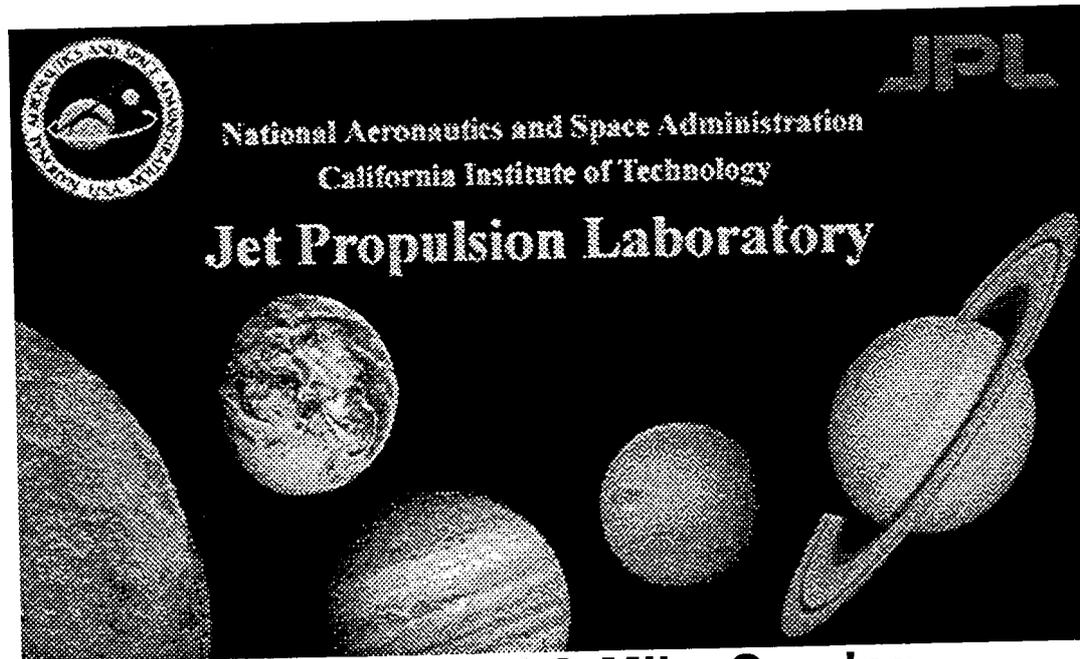


# Technology Management Symposium and Expo

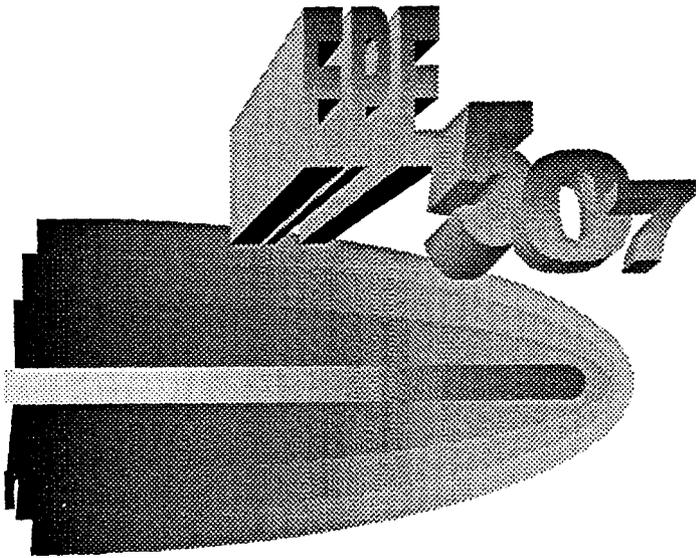
1997,

Commercial Off-The-Shelf (COTS)  
Search for Low Power Space  
Electronic Parts (LPSEP) - COTS Parts  
Evaluation Results

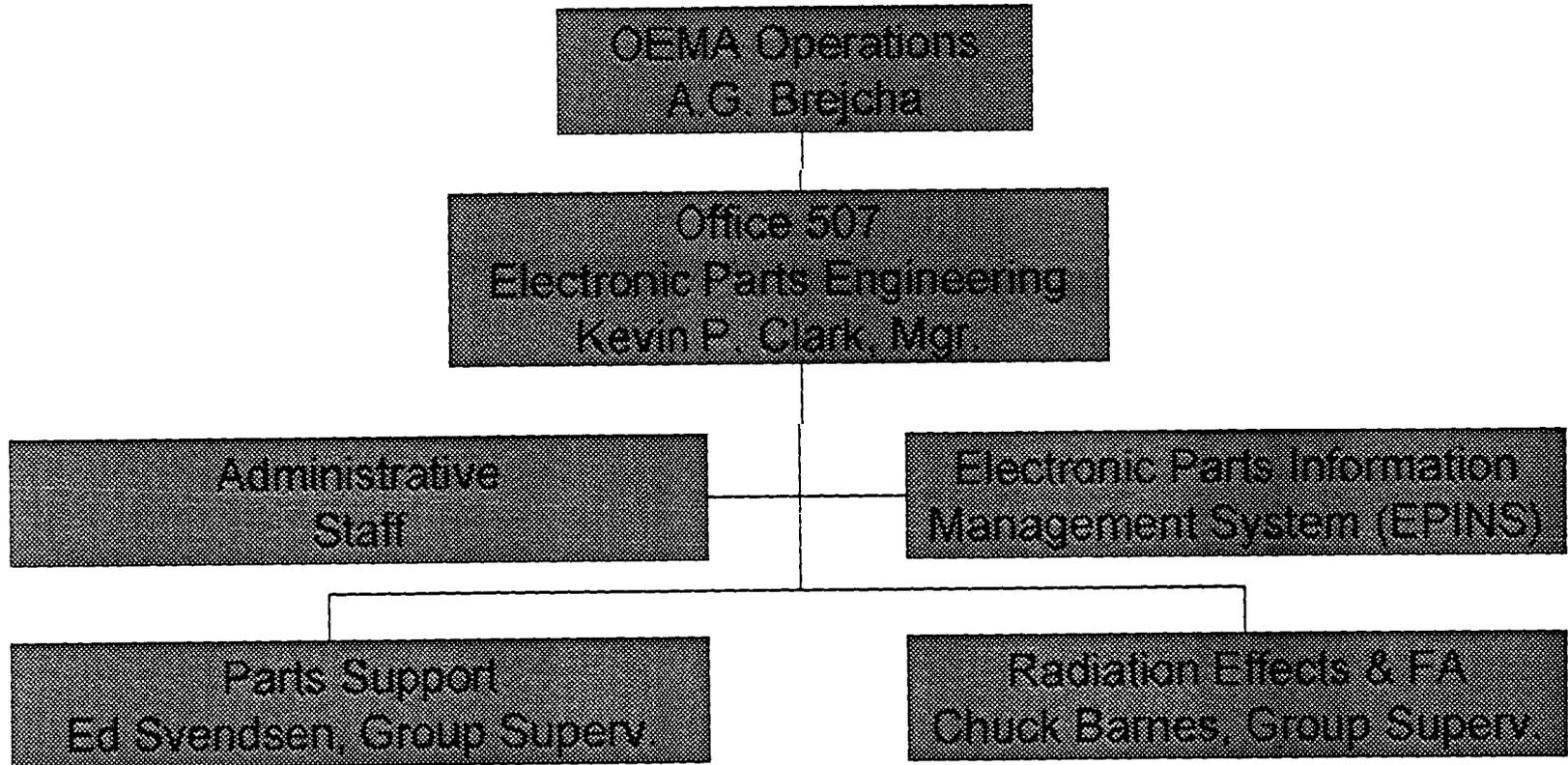


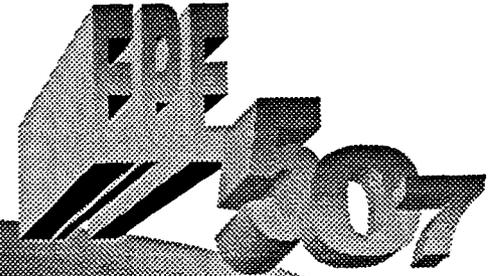
Shri Agarwal & Mike Sandor

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# Organization





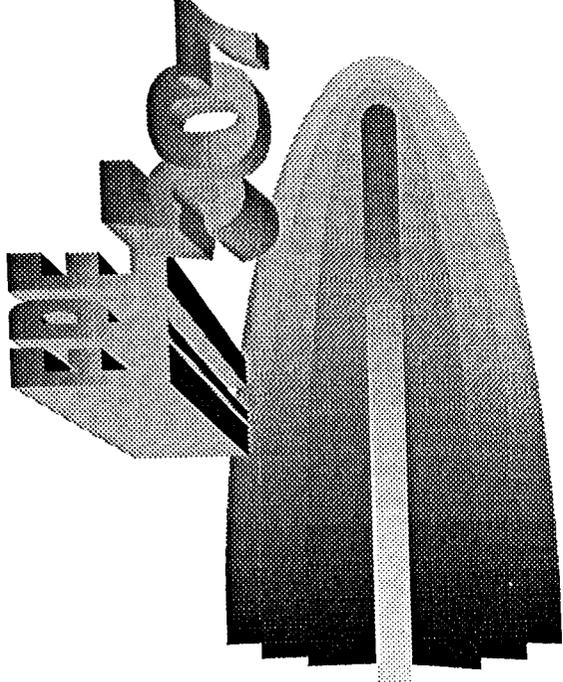
## Agenda

Low Power (LP) Parts in Space

Achieving Low Power

Parts Evaluation Results

Summary

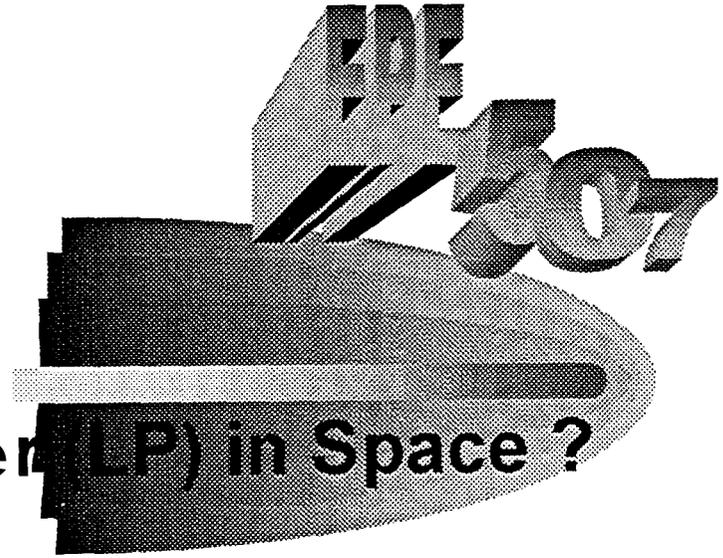


## The Meaning of COTS

- “Buy and Fly”
- “Procuring via catalog part number to QML-V standards”
- “Procurement is performed without formal specifications”
- “The usage of any COTS equipment does not constitute any waiver to fundamental applicable requirements”

## Our Interpretation:

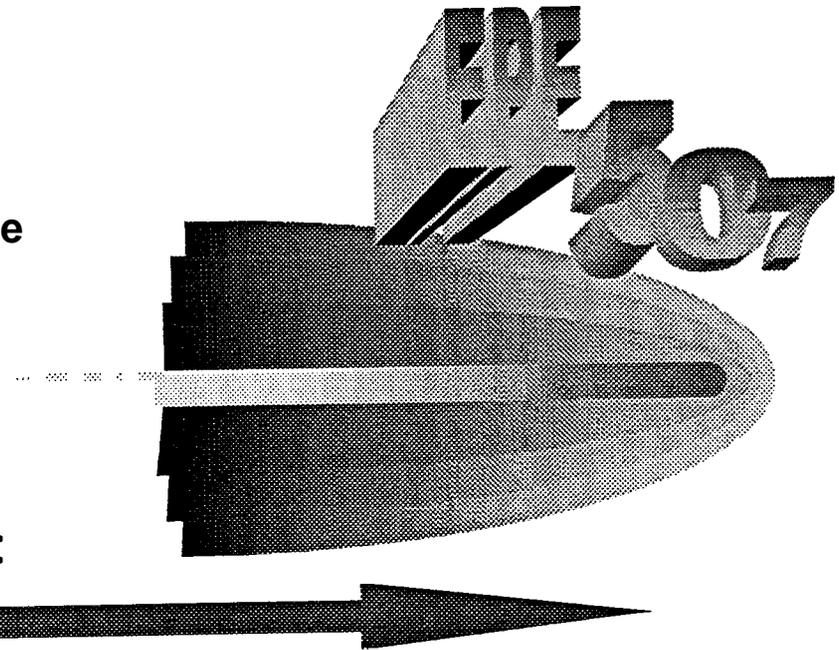
COTS are parts whose specification is manufacturer-controlled as opposed to traditional “Hi-Rel” parts whose specification was Government or customer-controlled



## **Why Put COTS Low Power (LP) in Space ?**

- 1. The availability of COTS LP parts is proliferating.**
- 2. COTS LP parts performance capabilities continue to increase (e.g. processing power & high density memories).**
- 3. A new generation of leading COTS LP IC technologies is forthcoming: Bulk CMOS/RH & Silicon-On-Insulator (SOI).**
- 4. COTS LP parts typically cost much less than radiation hardened counterparts; by using radiation tolerant parts the cost advantage can be preserved.**
- 5. Some COTS LP parts (plastic only) have been reported to demonstrate good to excellent reliability.**

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**Spatecraft Power Migration:**

	<b>Cassini</b>	<b>Galileo</b>	<b>X2000</b>	<b>Mars Pathfinder</b>
<b>Power Source</b>	3 RTGs	2 RTGs	ARPS	Solar/Battery
<b>SC Power Usage/ Requirements</b>	<b>900</b> Watts	<b>600</b> Watts	150 Watts	<b>3- 12*</b> Watts (Rover)

Notes:

RTG: Radioisotope Thermoelectric Generator

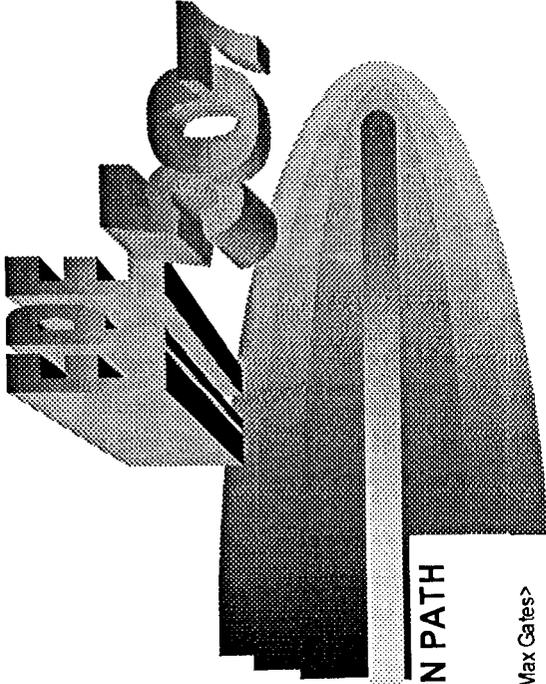
ARPS: Advanced Radioisotope Power Source

SC: Spacecraft

\* Dependent on the operational mode

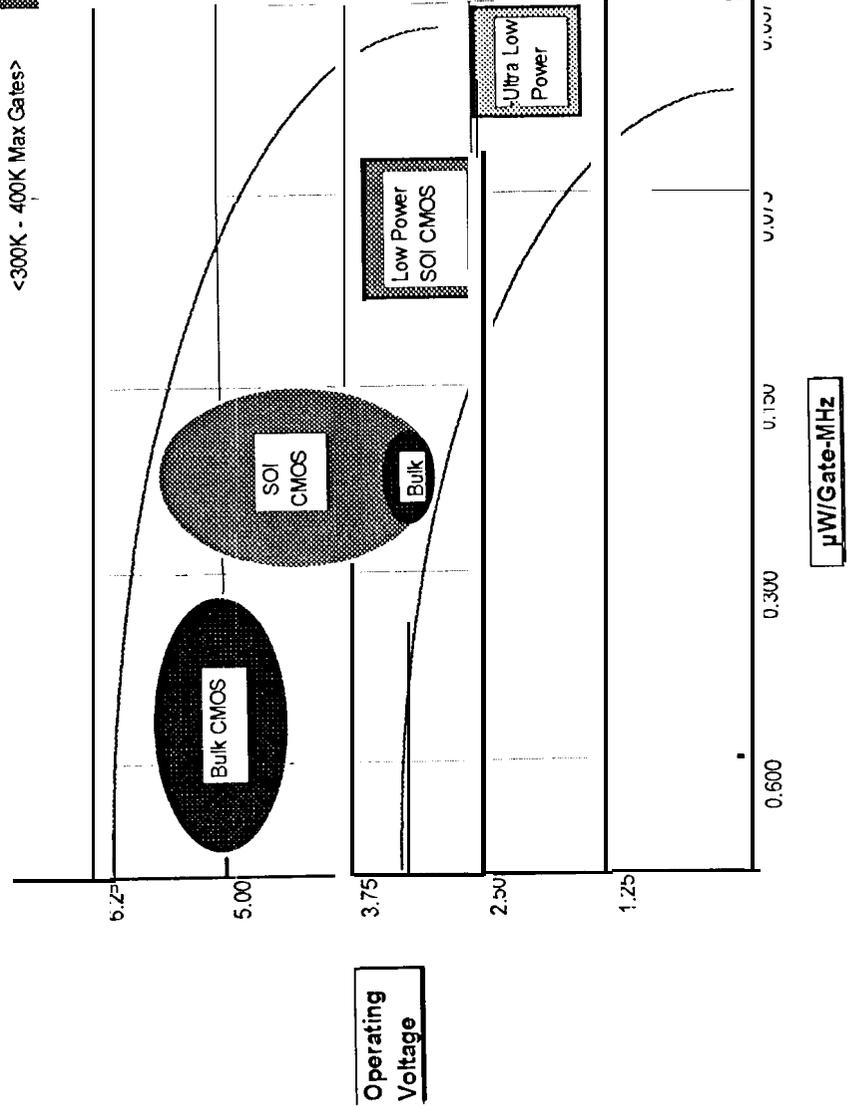
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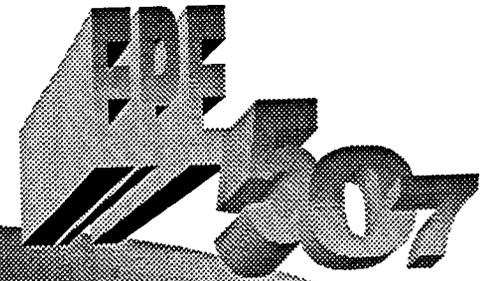
### LOW POWER TECHNOLOGY MIGRATION PATH

<300K - 400K Max Gates>

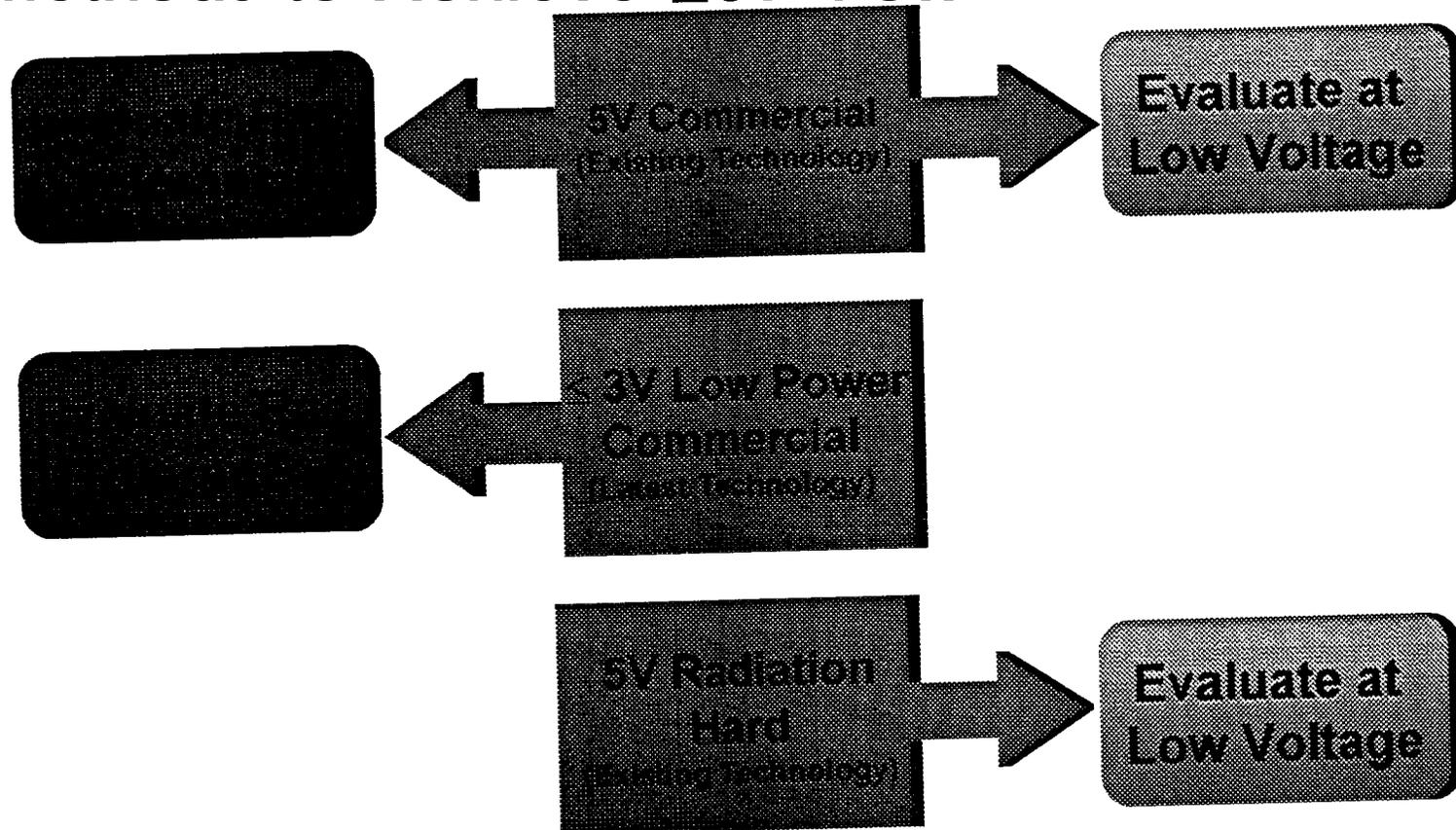


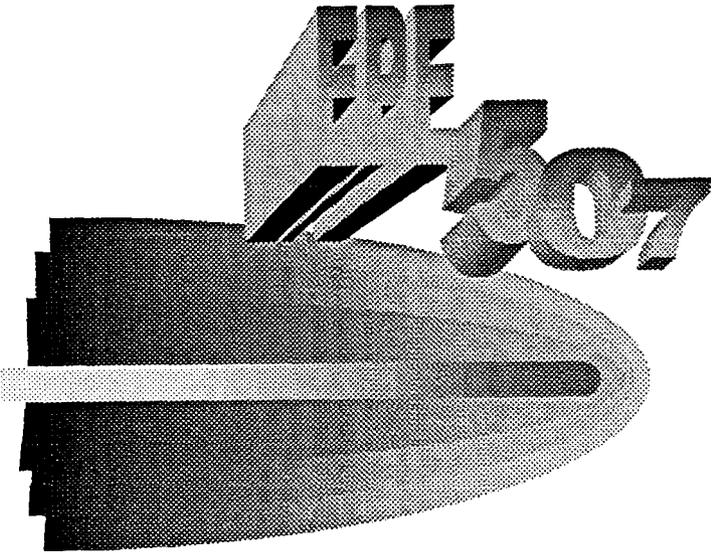
### Approaches:

1. Further Scaling of Structures for Conventional Bulk/RH
2. Thinner Si Active Regions for Silicon-On-Insulator
3. Ultra Thin Gate Dielectrics for Silicon-On-Insulator



# Methods to Achieve Low Power Parts:





## Reducing CMOS Device Power Dissipation:

{-----Dynamic Switching-----} {Short Circuit} {----de Static----}

$$\text{Power Equation: } P_{\rightarrow} = n_p C_{load} V_{out} V_{dd} f_{clock} + I_{sc} V_{dd} + I_{leakage} V_{dd}$$

$n_p$  = activity factor determined by power management schemes

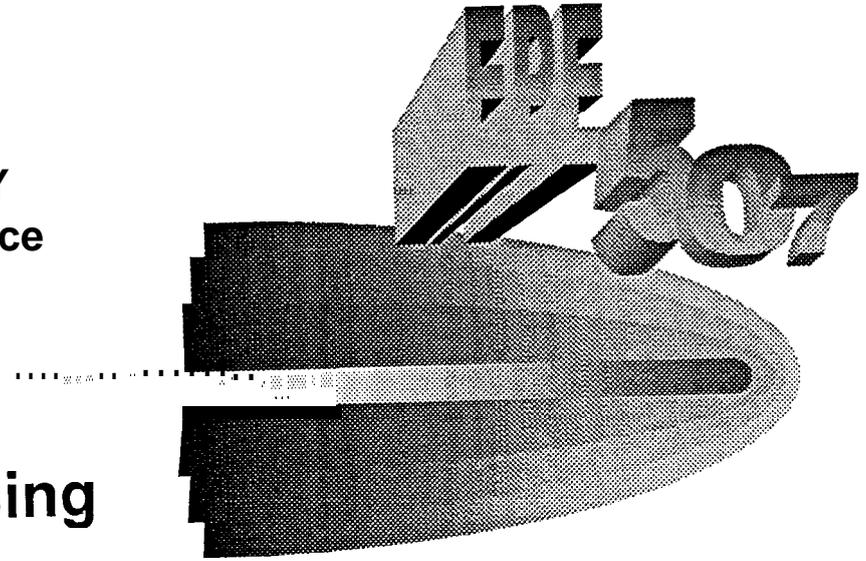
$I_{sc}$  = short circuit current during switching transient

$I_{leakage}$  = dc static current (junction leakage)

**Dominant Power Dissipation Factor: Dynamic Switching**

**Dominant Power Reduction Controls for User:**

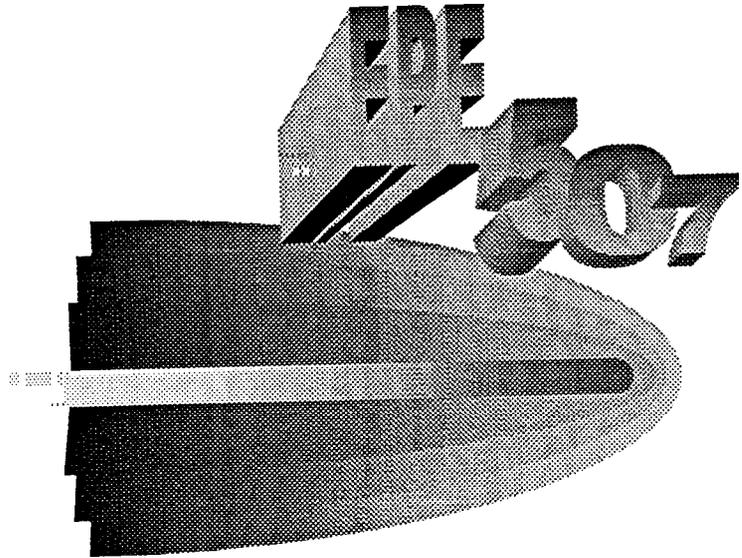
1.  $V_{dd}$  (supply voltage)
2.  $f$  (clock frequency & clock cycle)



## Issues To Consider When Using Low Voltage ( $V_{dd}$ ) Parts:

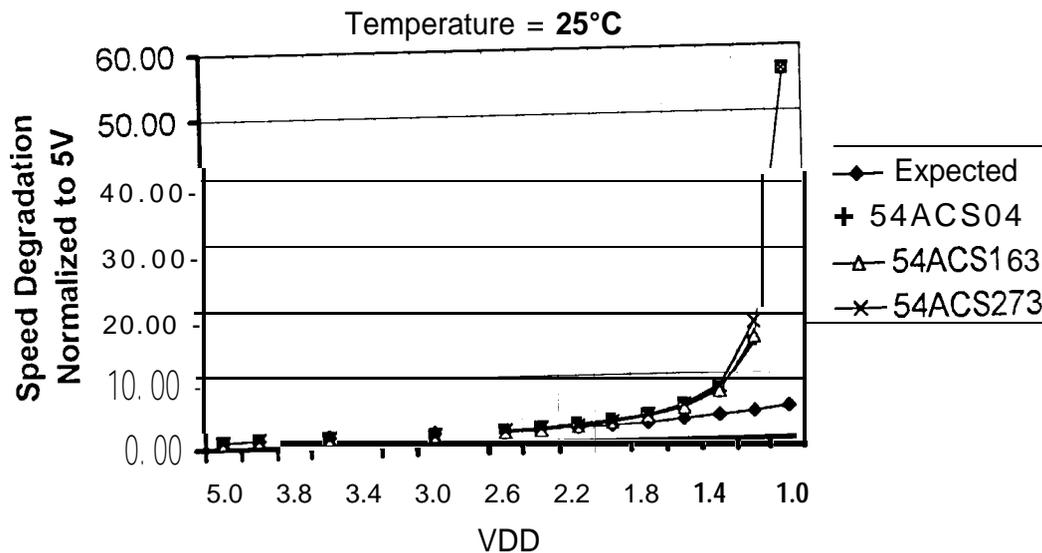
- Speed degradation
- Realized power savings vs theoretical
- Performance over temperature
- Radiation effects
- Increased signal to noise ratio
- Inadequate burn-in voltage and time
- Efficacy of applying derating factors

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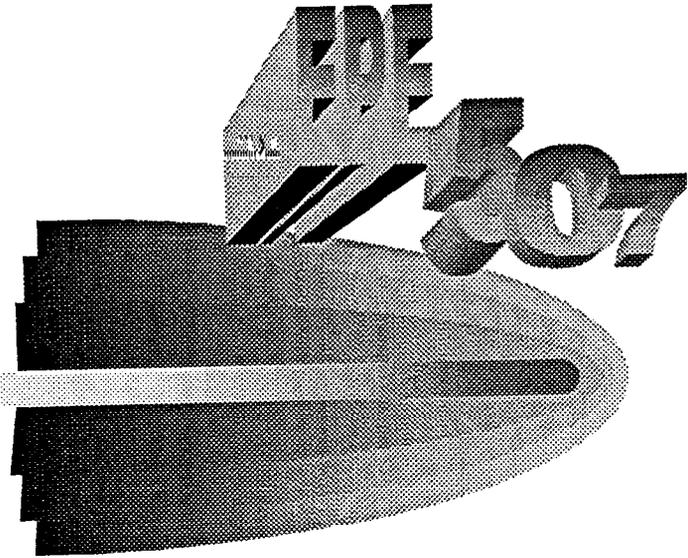
## Speed Degradation Results:

### Low Voltage Performance of 5V Radiation Hardened Products



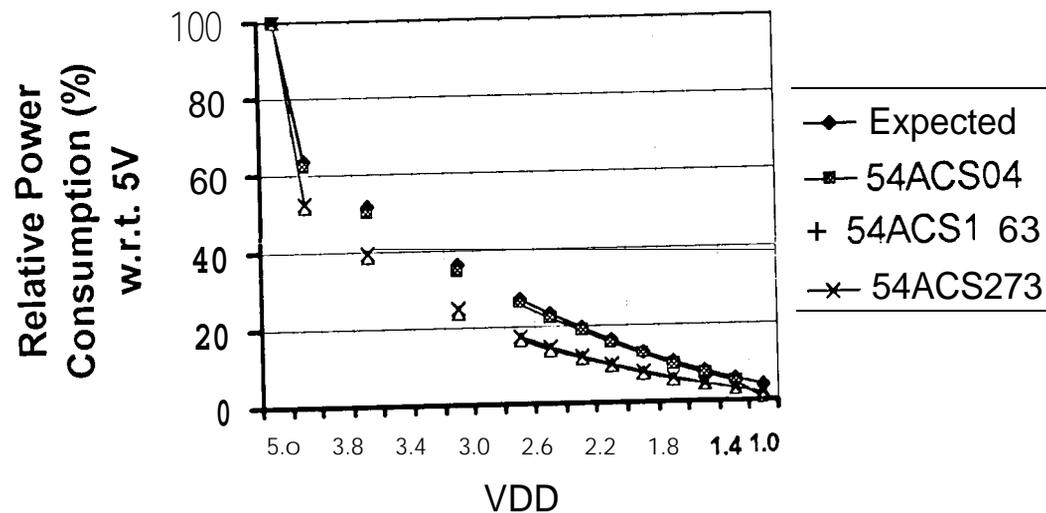
#### Notes:

1. **54ACS163** and **54ACS273** failed functional test at **VDD = 1.0V**.
2. Below **VDD = 2.5V** there is a **speed penalty over and above the expected degradation**.



## Realized Power Savings vs Theoretical Results:

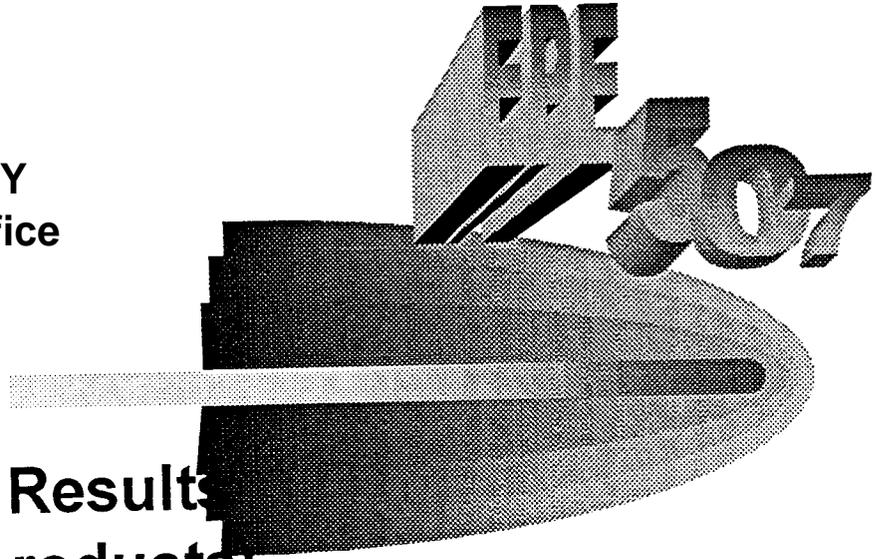
Relative Power Consumption of 5V  
Radiation Hardened Products



### Notes:

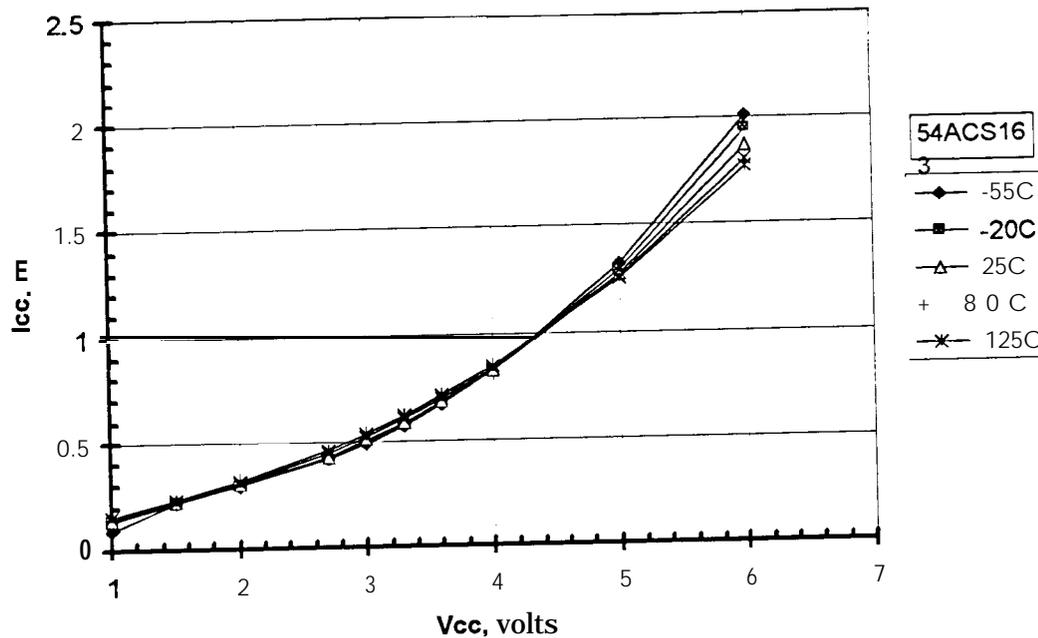
1. 54ACS163 and 54ACS273 are better than predicted.
2. 54ACS04 follows the prediction.
3. Power is calculated for each part using its dynamic current. The quiescent current contributions are negligible.

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# Temperature Compensation Results for 5V Radiation Hardened products:

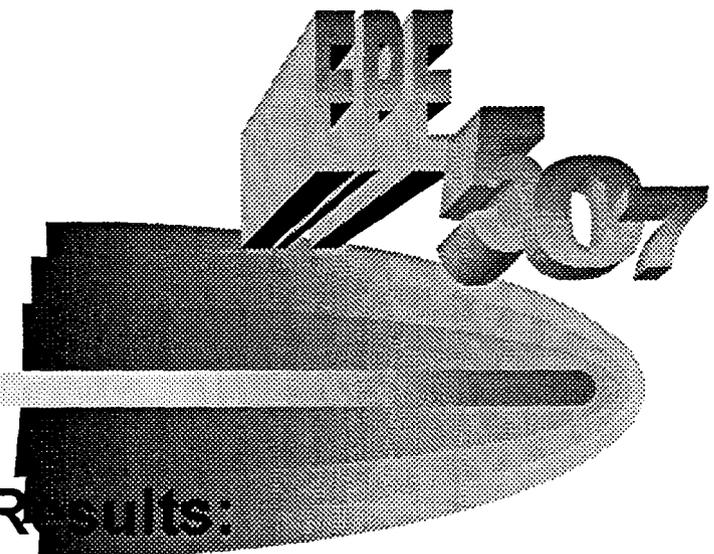
Dynamic Supply Current @ 10 MHz  
vs Vcc and Temperature



Notes:

1. AH 3 parts showed excellent temperature compensation for dynamic current in the low Vcc range.
2. At 6.0V, 15% w.c. divergence is observed for 54ACS163.

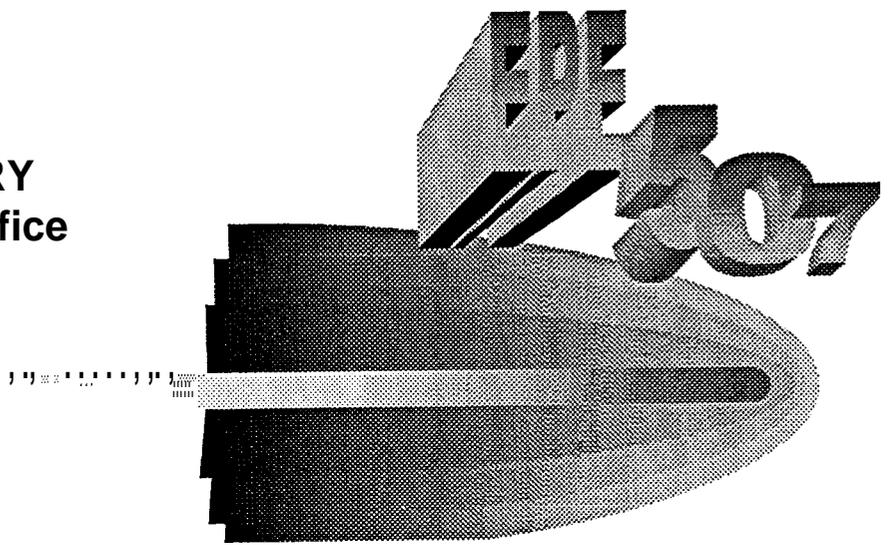
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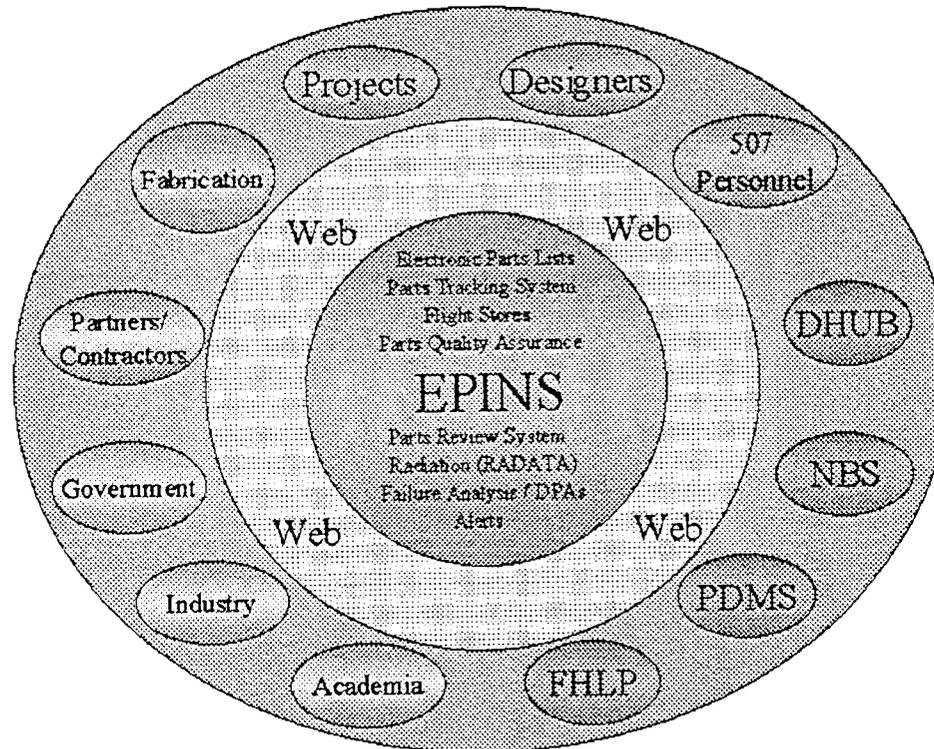
## AID Low Power COTS Radiation Results:

<b>PIN</b>	<b>Resolution</b>	<b>Process</b>	<b>VDD</b>	<b>Power</b>	<b>Speed</b>	<b>Total Dose</b>	<b>SEL</b>
LTC1419	14-Bit	CMOS	+/- 5V	150 mW	800 Ksps	TBD	None, LET>600 MeV/mg/cm <sup>2</sup>
SPT7725	8-Bit	Bipolar	- 5.2V	2.2 W	300 Msps	>100 Krad (Si)	None, LETz100 MeV/mg/cm <sup>2</sup>
HI1276	8-Bit	Bipolar	- 5.2V	2.8 W	500 Msps	TBD	None, LET>100 Mev/mg/cm <sup>2</sup>
AD7714-3	24-Bit	CMOS	+ 3V	2.6 mW	100 Ksps	TBD	LET = 55 Mev/mg/cm <sup>2</sup>
ADS7809	16-Bit	CMOS	+ 5V	100 mW	100 Ksps	10 Krad (Si)	LET = 19.9 MeV/mg/cm <sup>2</sup>

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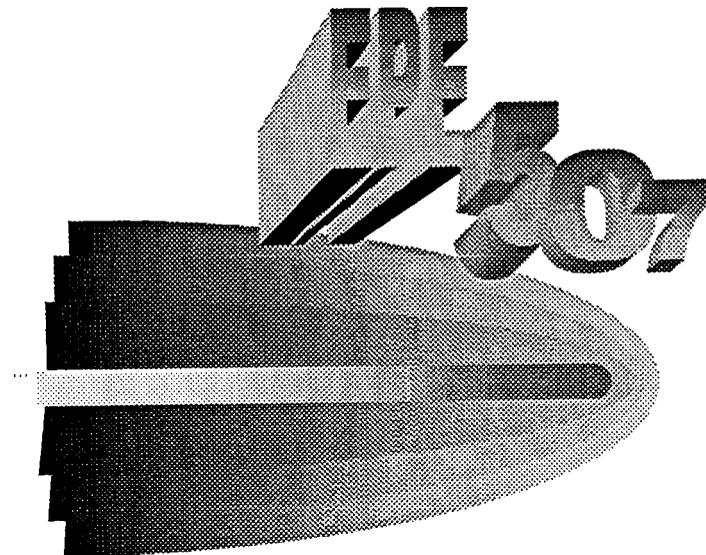


<http://parts.jpl.nasa.gov>



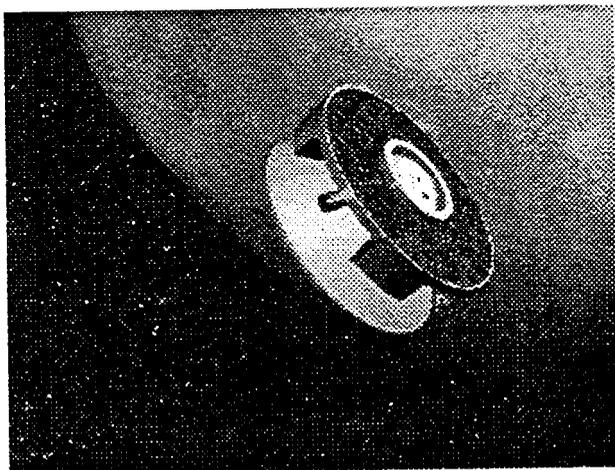
Electronic Parts Information Network System

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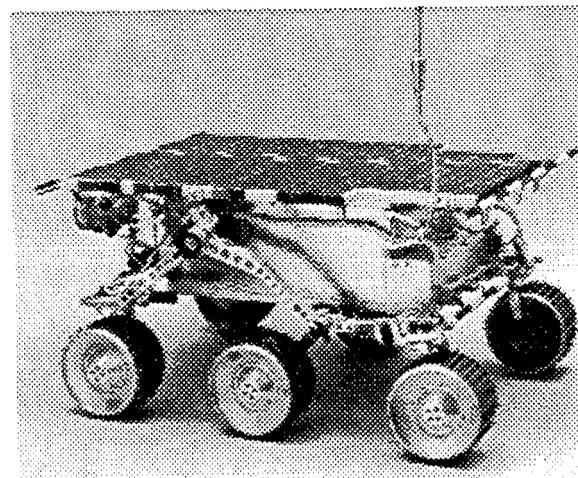


**Plastic Parts Successfully  
Used For Mars Pathfinder:**

16 Mbit DRAM Used in Pathfinder  
Flight Computer



FETs ; ASIC & Microcontroller  
Used in Modem for Lander and  
Rover



**Passed 1000 Hours Life Test on Mars!**



## Conelusion:

More power constraints in future Space designs will necessitate new techniques to reduce power consumption & improve performance via-

### Examples

1. Part selection → Lower voltage and power
2. Circuit design → Encoding of data or states
3. Architecture trade-off → Multi-level bus architectures
4. Power Management → Powering off selected bus nodes
5. Radiation Performance → Infusion of SOI technology